

### General Description

MBRF30150CT Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

### Features

- Common Cathode
- Multilayer Metal -Silicon Potential Structure
- Have Over Voltage protect loop, high reliability
- RoHS Compliant

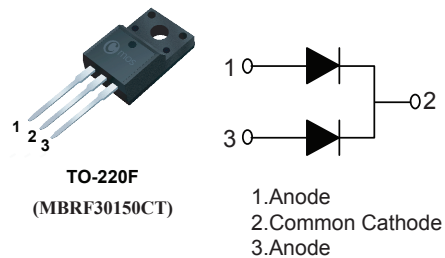
### Product Summary

$V_{RRM}$	$V_F$	$I_{F(AV)}$
150V	0.88V	30A

### Applications

- DC/DC converter
- Switched Mode Power Supplies (SMPS)
- Low Voltage High Frequency Invers Circuit

### TO-220F Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{RRM}$	Peak Repetitive Reverse Voltage	150	V
$I_{F(AV)}$	Average Rectified Forward Current (Rated VR-20Khz Square Wave) - 50% duty cycle	15 (Per Leg) 30 (Total)	A
dv/dt	Voltage rate of change (Rated VR)	10000	V/uS
$I_{RRM}$	Peak Repetitive Reverse Surge Current (2uS,1Khz)	0.5	A
$I_{FSM}$	Forward Peak Surge Current(Rated Load 8.3ms Half Mssine Wave-According to JEDEC Method)	340	A
$T_J$	Operating Junction Temperature	150	°C
$T_{STG}$	Storage Temperature	-40 to 150	°C

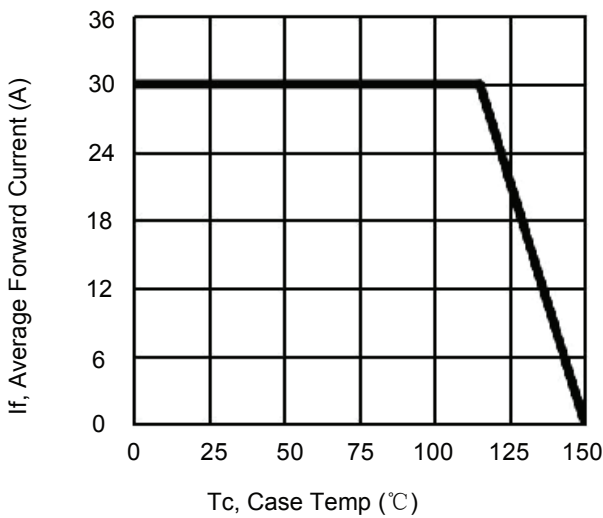
### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case(Per Leg)	4	---	°C/W

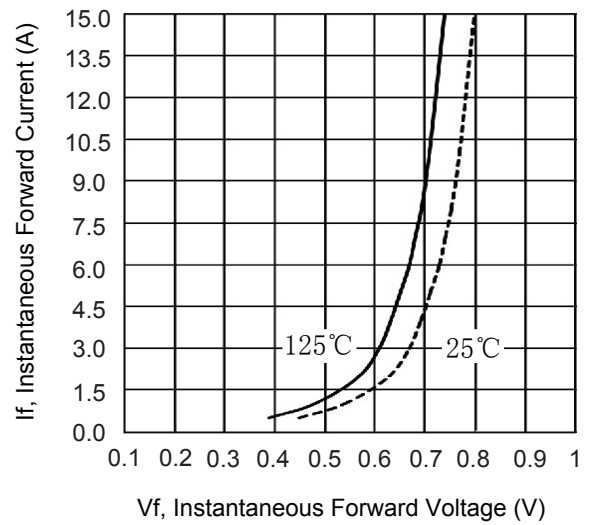
Electrical Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage Drop per diode	$I_F=15A, T_C=25^\circ C$	---	0.81	0.88	V
		$I_F=15A, T_C=125^\circ C$	---	---	0.76	
$I_R$	Reverse Leakage Current per diode	$V_R=150V, T_C=25^\circ C$	---	---	0.02	mA
		$V_R=150V, T_C=125^\circ C$	---	---	6	mA

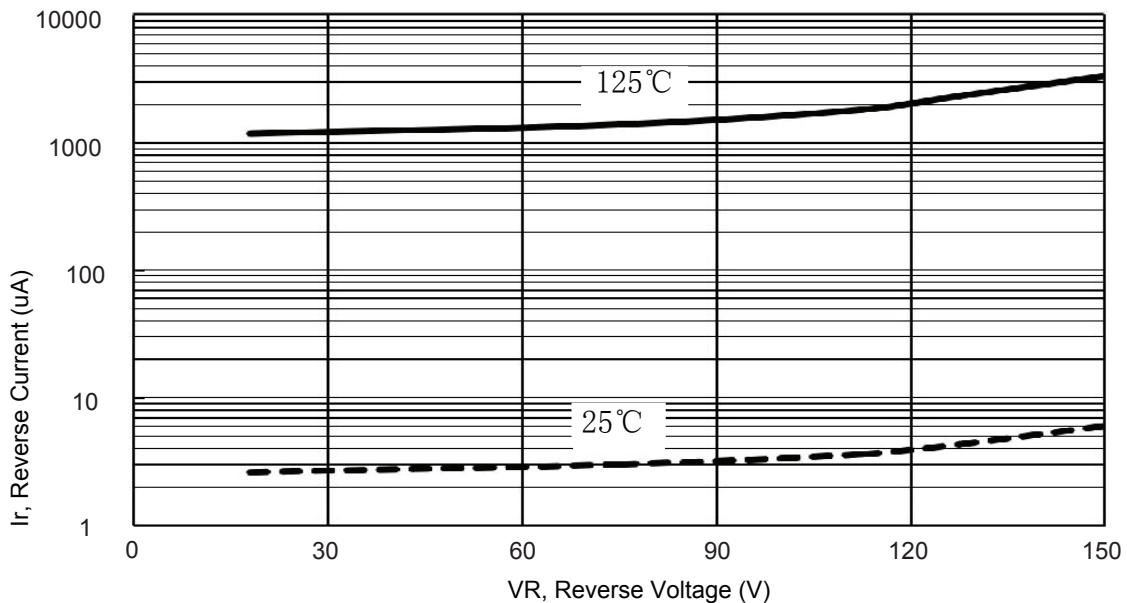
Typical Performance Characteristics



Current derating curve, per element



The forward voltage and forward current curve



The reverse leak current and the reverse voltage (single-device) curve

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